

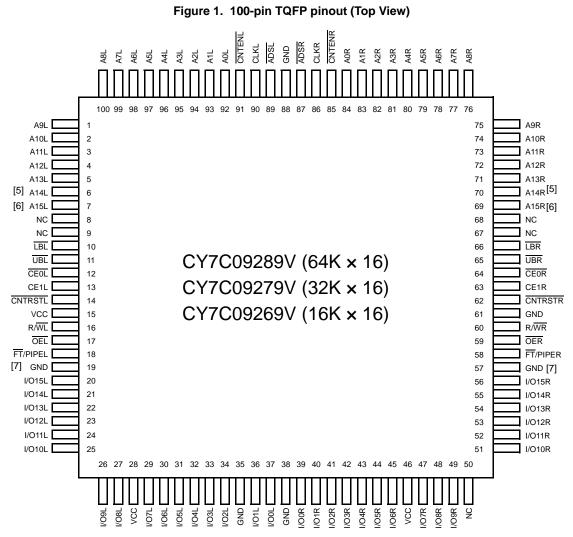
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Pin Configurations



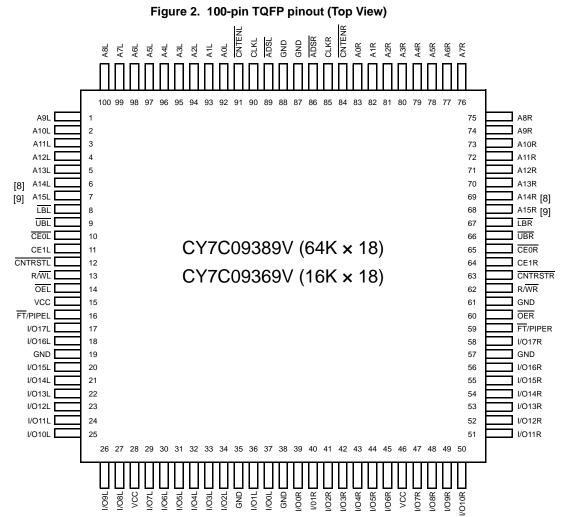
Notes

- 5. This pin is NC for CY7C09269V.
- 6. This pin is NC for CY7C09269V and CY7C09279V.

7. For CY7C09269V and CY7C09279V, pin #18 connected to V_{CC} is pin compatible to an IDT 5 V x 16 pipelined device; connecting pin #18 and #58 to GND is pin compatible to an IDT 5 V x 16 flow through device.



Pin Configurations (continued)



Notes

8. This pin is NC for CY7C09369V. 9. This pin is NC for CY7C09369V.



Selection Guide

Specifications	CY7C09269V/79V/89V CY7C09369V/89V	CY7C09269V/79V/89V CY7C09369V/89V	CY7C09269V/79V/89V CY7C09369V/89V
	-7 ^[10]	-9	-12
f _{MAX2} (MHz) (Pipelined)	83	67	50
Max. Access Time (ns) (Clock to Data, Pipelined)	7.5	9	12
Typical Operating Current I _{CC} (mA)	155	135	115
Typical Standby Current for I _{SB1} (mA) (Both Ports TTL Level)	25	20	20
Typical Standby Current for $I_{SB3}\left(\mu A\right)$ (Both Ports CMOS Level)	10	10	10

Pin Definitions

Left Port	Right Port	Description				
A _{0L} -A _{15L}	A _{0R} -A _{15R}	Address Inputs (A ₀ –A ₁₄ for 32K, A ₀ –A ₁₃ for 16K devices).				
ADSL	ADS _R	ddress Strobe Input. Used as an address qualifier. This signal must be asserted LOW to access the part using an externally supplied address. Asserting this signal LOW also loads the burst count with the address present on the address pins.				
CE _{0L} , CE _{1L}	CE _{0R} ,CE _{1R}	Chip Enable Input. To select either the left or right port, both \overline{CE}_0 AND CE_1 must be asserted to their active states ($\overline{CE}_0 \leq V_{IL}$ and $CE_1 \geq V_{IH}$).				
CLKL	CLK _R	Clock Signal. This input can be free running or strobed. Maximum clock input rate is f _{MAX} .				
CNTENL	CNTENR	Counter Enable Input. Asserting this signal LOW increments the burst address counter of its respective port on each rising edge of CLK. CNTEN is disabled if ADS or CNTRST are asserted LOW.				
CNTRSTL	CNTRSTR	Counter Reset Input. Asserting this signal LOW resets the burst address counter of its respective port to zero. CNTRST is not disabled by asserting ADS or CNTEN.				
I/O _{0L} -I/O _{17L}	I/O _{0R} -I/O _{17R}	Data Bus Input/Output (I/O ₀ -I/O ₁₅ for x 16 devices).				
LBL	LB _R	Lower Byte Select Input . Asserting this signal LOW enables read and write operations to the lower <u>byte</u> . ($I/O_0-I/O_8$ for x 18, $I/O_0-I/O_7$ for x 16) of the memory array. For read operations both the LB and OE signals must be asserted to drive output data on the lower byte of the data pins.				
UBL	UB _R	Upper Byte Select Input. Same function as \overline{LB} , but to the upper byte (I/O _{8/9L} -I/O _{15/17L}).				
OEL	OE _R	Output Enable Input. This signal must be asserted LOW to enable the I/O data pins during read operations.				
R/WL	R/WR	Read/Write Enable Input . This signal is asserted LOW to write to the dual port memory array. For read operations, assert this pin HIGH.				
FT/PIPE _L	FT/PIPE _R	Flow Through/Pipelined Select Input. For flow through mode operation, assert this pin LOW. For pipelined mode operation, assert this pin HIGH.				
GND		Ground Input.				
NC		No Connect.				
V _{CC}		Power Input.				



Functional Overview

The CY7C09269V/79V/89V and CY7C09369V/89V are high speed 3.3 V synchronous CMOS 16K, 32K, and 64K × 16 and 16K and 64K × 18 dual-port static RAMs. Two ports are provided, permitting independent, simultaneous access for reads and writes to any location in memory ^[11]. Registers on control, address, and data lines allow for minimal setup and hold times. In pipelined output mode, data is registered for decreased cycle time and clock to data valid t_{CD2} = 7.5 ns ^[12] (pipelined). Flow through mode can also be used to bypass the pipelined output register to eliminate access latency. In flow through mode, data is available t_{CD1} = 18 ns after the address is clocked into the device. Pipelined output or flow through mode is selected through the FT/Pipe pin.

Each port contains a burst counter on the input address register. The internal write pulse width is independent of the LOW to HIGH transition of the clock signal. The internal write pulse is self timed to allow the shortest possible cycle times. A HIGH on \overline{CE}_0 or LOW on CE_1 for one clock cycle powers down the internal circuitry to reduce the static power consumption. The use of multiple Chip Enables enables easier banking of multiple chips for depth expansion <u>configurations</u>. In the pipelined mode, one cycle is required with \overline{CE}_0 LOW and \overline{CE}_1 HIGH to reactivate the outputs.

Counter enable inputs are provided to stall the operation of the address input and use the internal address generated by the internal counter for fast interleaved memory applications. A <u>port's</u> burst counter is loaded with th<u>e port's</u> Address Strobe (ADS). When the port's Count Enable (CNTEN) is asserted, the address counter increments on each LOW to HIGH transition of that port's clock signal. This reads/writes <u>one word</u> from or into each successive address location, until CNTEN is deasserted. The counter can address th<u>e entire memory array</u> and loop back to the start. Counter Reset (CNTRST) is used to reset the burst counter.

All parts are available in 100-pin Thin Quad Plastic Flatpack (TQFP) packages.

Notes

11. When writing simultaneously to the same location, the final value cannot be guaranteed.

12. See Figure 4 on page 8 for Load Conditions.



Maximum Ratings

Exceeding maximum ratings ^[13] may impair the useful life of the device. These user guidelines are not tested.

Storage Temperature65 °C to +150 °C
Ambient Temperature with Power Applied55 °C to +125 °C
Supply Voltage to Ground Potential–0.5 V to +4.6 V
DC Voltage Applied to Outputs in High Z State–0.5 V to V_{CC} + 0.5 V

DC Input Voltage	–0.5 V to V _{CC} + 0.5 V
Output Current into Outputs (LOW)	20 mA
Static Discharge Voltage (per MIL-STD-883, Method 3015)	> 1100 V
Latch up Current	> 200 mA

Operating Range

Range	Ambient Temperature	V _{CC}
Commercial	0 °C to +70 °C	$3.3~V\pm300~mV$
Industrial	–40 °C to +85 °C	$3.3~V\pm300~mV$

Electrical Characteristics

Over the Operating Range

		CY7C09269V/79V/89V CY7C09369V/89V										
Parameter	Description			-7 ^[14]		-9			-12			Unit
			Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	
V _{OH}	Output HIGH Voltage (V_{CC} = Min, I_{OH}	= -4.0 mA)	2.4	_	-	2.4	-	-	2.4	_	-	V
V _{OL}	Output LOW Voltage (V_{CC} = Min, I_{OH}	= +4.0 mA)	_	_	0.4	-	_	0.4	-	_	0.4	V
V _{IH}	Input HIGH Voltage		2.0	-	-	2.0	-	-	2.0	-	-	V
V _{IL}	Input LOW Voltage		-	-	0.8	-	-	0.8	-	-	0.8	V
I _{OZ}	Output Leakage Current		-10	_	10	-10	_	10	-10	_	10	μΑ
I _{CC}	Operating Current	Commercial	-	155	275	-	135	230	-	115	180	mA
	(V _{CC} = Max, I _{OUT} = 0 mA) Outputs Disabled	Industrial	-	275	390	-	185	300	-	-	-	mA
I _{SB1}	Standby Current	Commercial	-	25	85	-	20	75	-	20	70	mA
	$\label{eq:bound} \frac{(Both Ports TTL Level)}{CE_L \& CE_R \geq V_{IH}, \ f = f_{MAX}}$	Industrial	-	85	120	-	35	85	-	-	-	mA
I _{SB2}	Standby Current	Commercial	-	105	165	-	95	155	-	85	140	mA
	$\label{eq:constraint} \frac{(One \ Port \ TTL \ Level)^{[15]}}{CE_L \ \ CE_R \ge V_{IH}, \ f = f_{MAX}}$	Industrial	Ι	165	210	Ι	105	165	Ι	-	Ι	mA
I _{SB3}	Standby Current	Commercial	-	10	250	-	10	250	-	10	250	μΑ
	$\label{eq:bound} \frac{(Both \ Ports \ CMOS \ Level)}{CE_L \ \& \ CE_R \ge V_{CC} - 0.2 \ V, \ f = 0}$	Industrial	Ι	10	250	Ι	10	250	Ι	-	Ι	μΑ
I _{SB4}	Standby Current	Commercial	-	95	125	-	85	115	-	75	100	mA
	$\label{eq:constraint} \frac{(One \ Port \ CMOS \ Level)}{CE_L \ \ CE_R \ge V_{IH}, \ f = f_{MAX}} $	Industrial	Ι	125	170	-	95	125	-	_	Ι	mA

Capacitance

Parameter ^[16]	Description	Test Conditions	Мах	Unit
C _{IN}	Input Capacitance	$T_A = 25 \text{ °C}, f = 1 \text{ MHz}, V_{CC} = 3.3 \text{ V}$	10	pF
C _{OUT}	Output Capacitance		10	pF

Notes

13. The voltage on any input or I/O pin can not exceed the power pin during power up.

14. See Figure 4 on page 8 for Load Conditions.

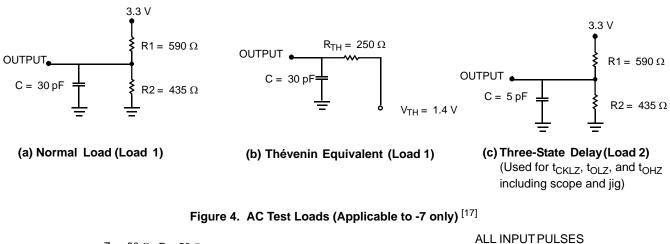
15. \overline{CE}_{L} and \overline{CE}_{R} are internal signals. To select either the left or right port, both \overline{CE}_{0} and CE_{1} must be asserted to their active states ($\overline{CE}_{0} \leq V_{IL}$ and $CE_{1} \geq V_{IH}$).

16. Tested initially and after any design or process changes that may affect these parameters.

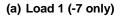


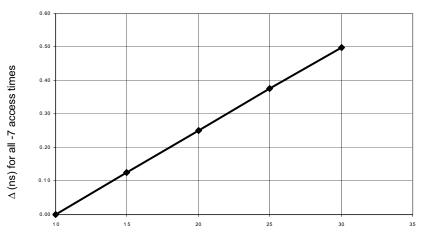
AC Test Loads and Waveforms

Figure 3. AC Test Loads and Waveforms









Capacitance (pF)

(b) Load Derating Curve

Note 17. Test Conditions: C = 10 pF.



Switching Characteristics

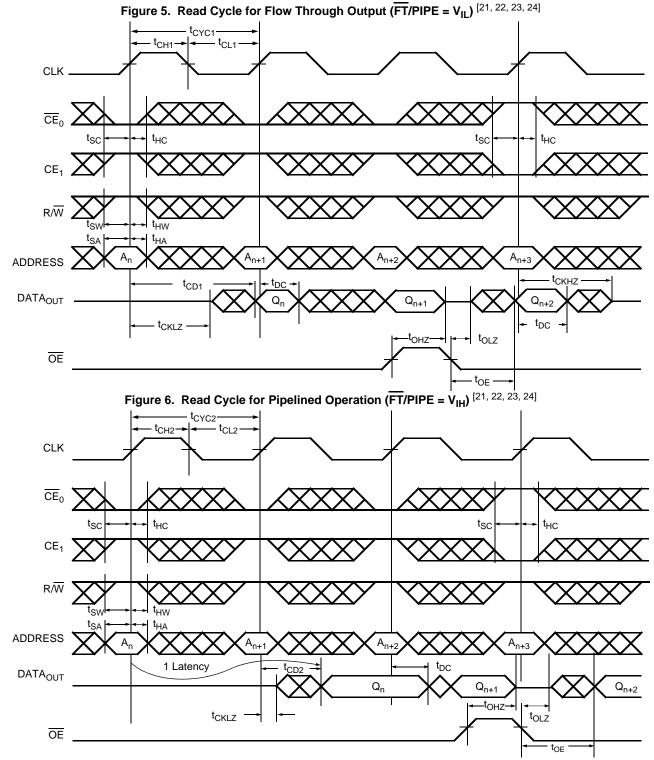
Over the Operating Range

		CY7C09269V/79V/89V CY7C09369V/89V						
Parameter	Description	-7	[18]	-	.9	-	12	Unit
4		Min	Max	Min	Max	Min	Max	
f _{MAX1}	f _{Max} Flow Through	-	45	-	40	_	33	MHz
f _{MAX2}	f _{Max} Pipelined	-	83	-	67	-	50	MHz
t _{CYC1}	Clock Cycle Time - Flow Through	22	-	25	-	30	-	ns
t _{CYC2}	Clock Cycle Time - Pipelined	12	-	15	-	20	-	ns
t _{CH1}	Clock HIGH Time - Flow Through	7.5	-	12	-	12	-	ns
t _{CL1}	Clock LOW Time - Flow Through	7.5	-	12	-	12	-	ns
t _{CH2}	Clock HIGH Time - Pipelined	5	-	6	-	8	-	ns
t _{CL2}	Clock LOW Time - Pipelined	5	-	6	-	8	-	ns
t _R	Clock Rise Time	-	3	-	3	-	3	ns
t _F	Clock Fall Time	-	3	-	3	-	3	ns
t _{SA}	Address Set-Up Time	4	-	4	-	4	-	ns
t _{HA}	Address Hold Time	0	-	1	_	1	-	ns
t _{SC}	Chip Enable Setup Time	4	-	4	_	4	-	ns
t _{HC}	Chip Enable Hold Time	0	-	1	_	1	-	ns
t _{SW}	R/W Set-Up Time	4	-	4	_	4	-	ns
t _{HW}	R/W Hold Time	0	-	1	_	1	-	ns
t _{SD}	Input Data Setup Time	4	-	4	_	4	-	ns
t _{HD}	Input Data Hold Time	0	-	1	_	1	-	ns
t _{SAD}	ADS Set-Up Time	4	-	4	-	4	-	ns
t _{HAD}	ADS Hold Time	0	-	1	_	1	-	ns
t _{SCN}	CNTEN Setup Time	4.5	-	5	-	5	_	ns
t _{HCN}	CNTEN Hold Time	0	_	1	_	1	_	ns
t _{SRST}	CNTRST Setup Time	4	_	4	_	4	_	ns
t _{HRST}	CNTRST Hold Time	0	-	1	-	1	_	ns
t _{OE}	Output Enable to Data Valid	-	9	-	10	_	12	ns
t _{OLZ} ^[19, 20]	OE to Low Z	2	_	2	_	2	_	ns
t _{OHZ} ^[19, 20]	OE to High Z	1	7	1	7	1	7	ns
t _{CD1}	Clock to Data Valid - Flow Through	_	18	-	20	_	25	ns
t _{CD2}	Clock to Data Valid - Pipelined	-	7.5	-	9	-	12	ns
t _{DC}	Data Output Hold After Clock HIGH	2	-	2	-	2	-	ns
t _{СКНZ} ^[19, 20]	Clock HIGH to Output High Z	2	9	2	9	2	9	ns
t _{CKLZ} ^[19, 20]	Clock HIGH to Output Low Z	2	_	2	-	2	_	ns
Port to Port I	Delays	1	1	1	I	1	1	1
t _{CWDD}	Write Port Clock HIGH to Read Data Delay	-	35	-	40	-	40	ns
t _{CCS}	Clock to Clock Setup Time	-	10	-	15	-	15	ns

Notes18. See Figure 4 on page 8 for Load Conditions.19. Test conditions used are Load 2.20. This parameter is guaranteed by design, but it is not production tested.



Switching Waveforms

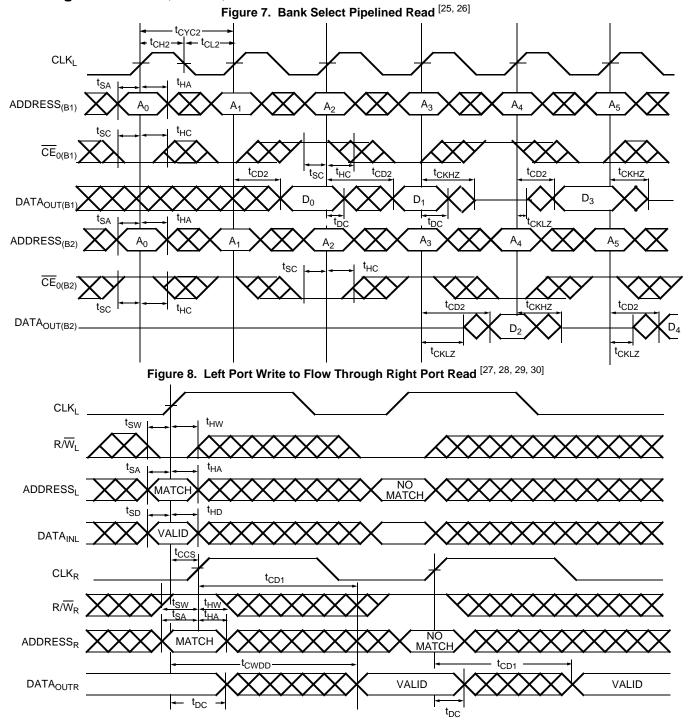


Notes

21. OE is asynchronously controlled; all other inputs are synchronous to the rising clock edge.

21. <u>DE is asylicitoriology contoned, an other inputs are sylicitoriology to the hourg stock edge.</u> 22. ADS = V_{IL} , <u>CNTEN and CNTRST</u> = V_{IH} . 23. The output is disabled (high impedance state) by $\overline{CE}_0 = V_{IH}$ or $\underline{CE}_1 = V_{IL}$ following the next rising edge of the clock. 24. Addresses do not have to be accessed sequentially since ADS = V_{IL} constantly loads the address on the rising edge of the CLK. Numbers are for reference only.

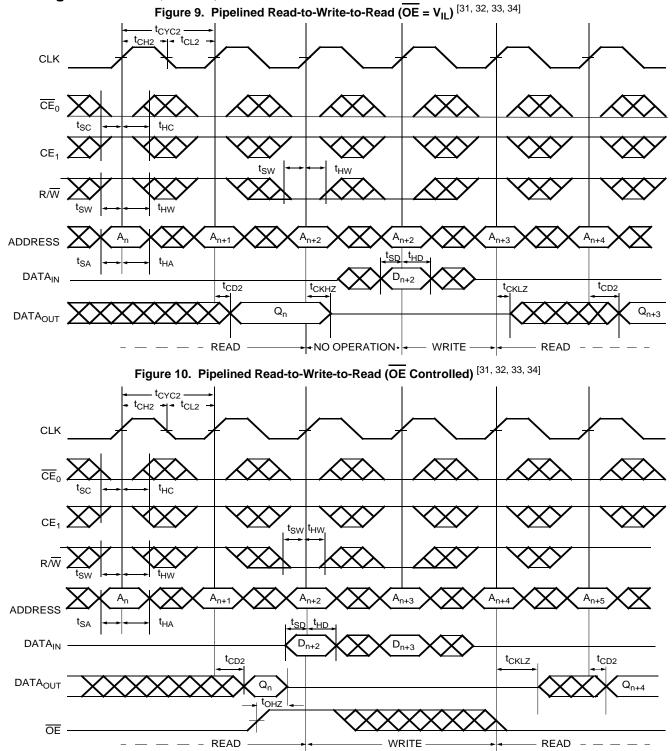




Notes

- Notes
 25. In this depth expansion example, B1 represents Bank #1 and B2 is Bank #2; Each Bank consists of one Cypress dual-port device from this datasheet. <u>ADDRESS_(B1) = <u>ADDRESS_(B2)</u>.
 26. UB, LB, OE and ADS = V_{IL}; CE_{1(B1)}, CE_{1(B2)}, RW, CNTEN, and CNTRST = V_{IH}.
 27. The same waveforms apply for a right port write to flow through left port read.
 28. <u>CE₀</u>, UB, LB, and ADS = V_{IL}; CE₁, CNTEN, and CNTRST = V_{IH}.
 29. OE = V_{IL} for the Right Port, which is being read from. OE = V_{IH} for the Left Port, which is being written to.
 30. It t_{CCS} ≤ maximum specified, then data from right port READ is not valid until the maximum specified for t_{CWDD}. If t_{CCS}>maximum specified, then data is not valid until t_{CCS} + t_{CD1}. t_{CWDD} does not apply in this case.
 </u>





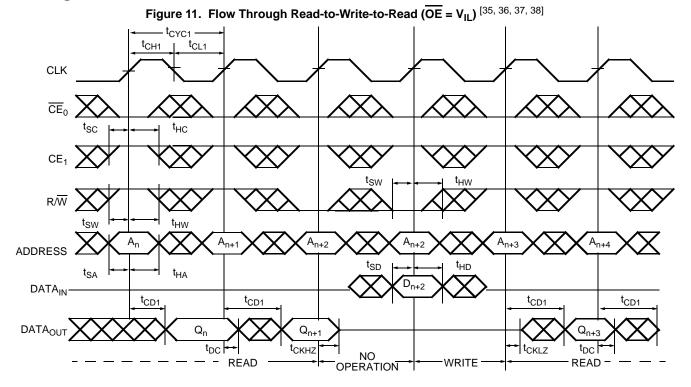
Notes

31. Addresses do not have to be accessed sequentially since $\overline{ADS} = V_{|L}$ constantly loads the address on the rising edge of the CLK. Numbers are for reference only. 32. Output state (High, LOW, or high impedance) is determined by the previous cycle control signals.

33. \overline{CE}_0 and $\overline{ADS} = V_{IL}$; CE_1 , \overline{CNTEN} , and $\overline{CNTRST} = V_{IH}$.

34. During "No Operation", data in memory at the selected address may be corrupted and must be rewritten to ensure data integrity.





Notes 35. $\overline{ADS} = V_{IL}$, \overline{CNTEN} and $\overline{CNTRST} = V_{IH}$. 36. $\overline{Addresses}$ do not have to be accessed sequentially since $\overline{ADS} = V_{IL}$ constantly loads the address on the rising edge of the CLK. Numbers are for reference only. 37. \overline{CE}_0 and $\overline{ADS} = V_{IL}$; \overline{CE}_1 , \overline{CNTEN} , and $\overline{CNTRST} = V_{IH}$. 38. During "No Operation", data in memory at the selected address may be corrupted and must be rewritten to ensure data integrity.

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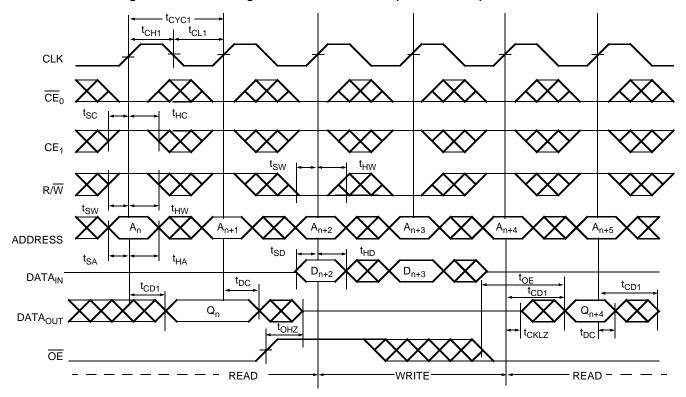


Figure 12. Flow Through Read-to-Write-to-Read (OE Controlled) ^[39, 40, 41, 42, 43]

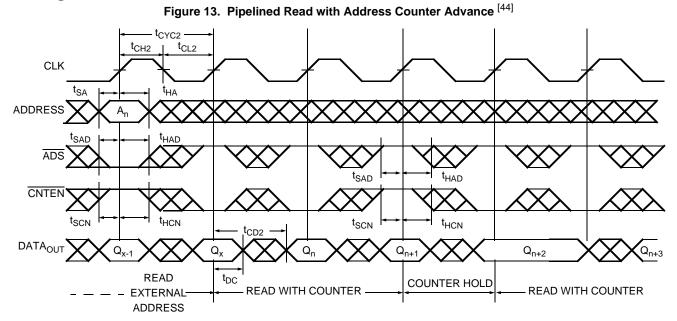
Notes 39. ADS = V_{IL} , CNTEN and CNTRST = V_{IH} .

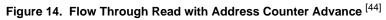
40. Addresses do not have to be accessed sequentially since ADS = V_{IL} constantly loads the address on the rising edge of the CLK. Numbers are for reference only.

41. CE₀ and ADS = V_{IL} ; CE₁, CNTEN, and CNTRST = V_{IL} . 42. During "No Operation", data in memory at the selected address may be corrupted and must be rewritten to ensure data integrity. 43. Output state (High, LOW, or high impedance) is determined by the previous cycle control signals.









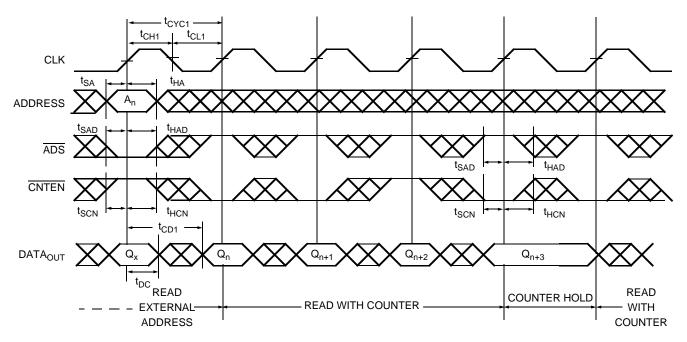
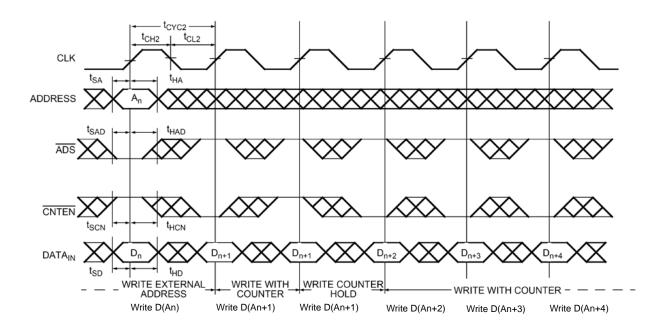


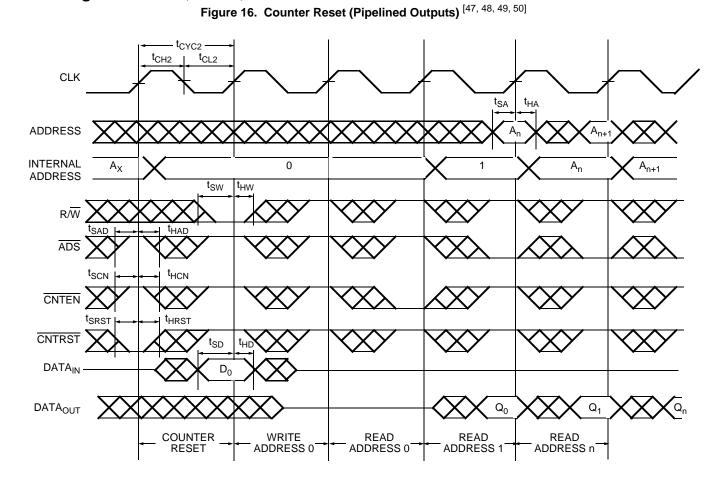


Figure 15. Write with Address Counter Advance (Flow Through or Pipelined Outputs) [45, 46]



Notes 45. $\overline{CE_0}$, \overline{UB} , \overline{LB} , and $\overline{R/W} = V_{IL}$; $\overline{CE_1}$ and $\overline{CNTRST} = V_{IH}$. 46. The "Internal Address" is equal to the "External Address" when $\overline{ADS} = V_{IL}$ and equals the counter output when $\overline{ADS} = V_{IH}$.





Notes

- 47. Addresses do not have to be accessed sequentially since $\overline{ADS} = V_{|L}$ constantly loads the address on the rising edge of the CLK. Numbers are for reference only. 48. Output state (High, LOW, or high impedance) is determined by the previous cycle control signals. 49. \overline{CE}_0 , UB, and LB = $V_{|L}$; $\overline{CE}_1 = V_{|H}$.

- 50. No dead cycle exists during counter reset. A READ or WRITE cycle may be coincidental with the counter reset.



Read/Write and Enable Operation

The Read/Write and Enable Operation is described as follows. [51, 52, 53]

		Inputs			Outputs	Operation
OE	CLK	CE0	CE ₁	R/W	1/0 ₀ -1/0 ₁₇	Operation
X	μ	Н	х	х	High Z	Deselected ^[54]
Х		Х	L	Х	High Z	Deselected ^[54]
X	Ļ	L	Н	L	D _{IN}	Write
L		L	Н	Н	D _{OUT}	Read ^[55]
Н	Х	L	Н	Х	High Z	Outputs Disabled

Address Counter Control Operation

The Address Counter Control Operation is described as follows. [51, 56, 57, 58]

Address	Previous Address	CLK	ADS	CNTEN	CNTRST	I/O	Mode	Operation
x	Х	Ļ	Х	Х	L	D _{out(0)}	Reset	Counter Reset to Address 0
A _n	Х	μ	L	Х	Н	D _{out(n)}	Load	Address Load into Counter
Х	A _n	Ļ	Н	Н	Н	D _{out(n)}	Hold	External Address Blocked — Counter Disabled
Х	A _n		Н	L	Н	D _{out(n+1)}	Increment	Counter Enabled — Internal Address Generation

- Notes 51. $\underline{``X"} = \underline{``Don't Care", ``H"} = V_{IH}, ``L" = V_{IL}.$
- 52. ADS, CNTEN, CNTRST = "Don't Care".
- 53. $\overline{\text{DE}}$ is an asynchronous input signal. 54. When $\overline{\text{CE}}$ changes state in the pipelined mode, deselection and read happen in the following clock cycle. 55. $\overline{\text{ADS}} = V_{|L|}$, $\overline{\text{CNTEN}}$ and $\overline{\text{CNTRST}} = V_{|H|}$. 56. $\overline{\text{CE}}_0$ and $\overline{\text{OE}} = V_{|L|}$; $\overline{\text{CE}}_1$ and $\overline{\text{RW}} = V_{|H|}$.

- 57. Data shown for flow through mode; pipelined mode output is delayed by one cycle. 58. Counter operation is independent of \overline{CE}_0 and \overline{CE}_1 .

Document Number: 38-06056 Rev. *M



Ordering Information

16K × 16 3.3 V Synchronous Dual-Port SRAM

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
9	CY7C09269V-9AXC	51-85048	100-pin TQFP (Pb-free)	Commercial

32K × 16 3.3 V Synchronous Dual-Port SRAM

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
7.5 ^[59]	CY7C09279V-7AXC	51-85048	100-pin TQFP (Pb-free)	Commercial
12	CY7C09279V-12AXC	51-85048	100-pin TQFP (Pb-free)	Commercial

64K × 16 3.3 V Synchronous Dual-Port SRAM

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
9	CY7C09289V-9AXC	51-85048	100-pin TQFP (Pb-free)	Commercial
	CY7C09289V-9AXI	51-85048	100-pin TQFP (Pb-free)	Industrial
12	CY7C09289V-12AXC	51-85048	100-pin TQFP (Pb-free)	Commercial

16K × 18 3.3 V Synchronous Dual-Port SRAM

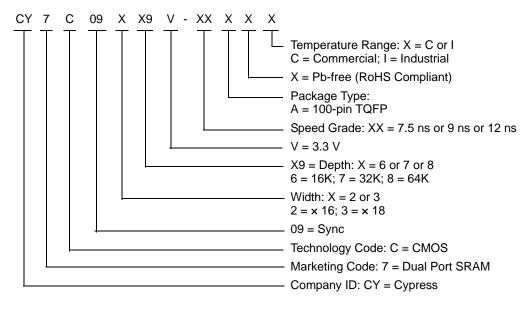
Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
12	CY7C09369V-12AXC	51-85048	100-pin TQFP (Pb-free)	Commercial

64K × 18 3.3 V Synchronous Dual-Port SRAM

Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
9	CY7C09389V-9AI	51-85048	100-pin TQFP	Industrial



Ordering Code Definitions

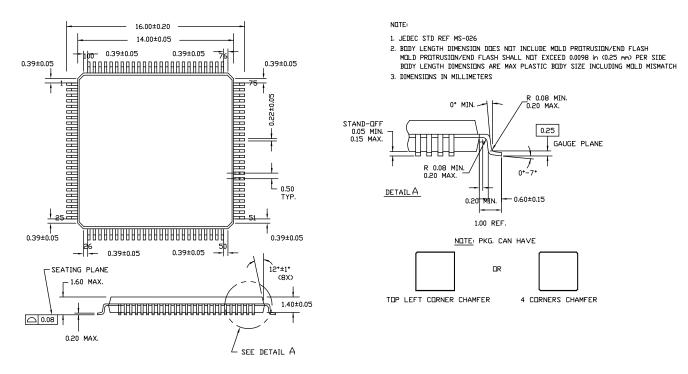




CY7C09269V/79V/89V CY7C09369V/89V

Package Diagrams





51-85048 *J



Acronyms

Acronym	Description
CE	Chip Enable
CMOS	Complementary Metal Oxide Semiconductor
I/O	Input/Output
OE	Output Enable
SRAM	Static Random Access Memory
TQFP	Thin Quad Flat Pack
TTL	Transistor-Transistor Logic

Document Conventions

Units of Measure

Symbol	Unit of Measure
°C	degree Celsius
MHz	megahertz
μA	microampere
mA	milliampere
mm	millimeter
mV	millivolt
ns	nanosecond
Ω	ohm
%	percent
pF	picofarad
V	volt



Document History Page

Revision	ECN	Submission Date	Orig. of Change	Description of Change
**	110215	12/18/01	SZV	Change from Spec number: 38-00668 to 38-06056
*A	122306	12/27/02	RBI	Updated Maximum Ratings: Added Power up requirements.
*В	344354	See ECN	PCX	Updated Ordering Information (Added Pb-Free Parts).
*C	2678221	03/25/2009	VKN / AESA	Updated Ordering Information (Added CY7C09379V-12AXCT part). Updated Package Diagrams (updated spec 51-85048 to *C).
*D	2896210	03/22/2010	RAME	Updated Ordering Information. Updated Package Diagrams.
*E	3111417	12/15/2010	ADMU	Updated Ordering Information. Added Ordering Code Definitions.
*F	3124048	12/30/2010	ADMU	No technical updates.
*G	3352110	08/23/2011	ADMU	Updated Features (Removed CY7C09379V information and also removed -6 speed bin information). Updated Pin Configurations (Removed CY7C09379V information). Updated Selection Guide (Removed CY7C09379V information and also removed -6 speed bin information). Updated Functional Overview (Removed CY7C09379V information). Updated Electrical Characteristics (Removed CY7C09379V information and also removed -6 speed bin information). Updated AC Test Loads and Waveforms (Removed -6 speed bin information). Updated Switching Characteristics (Removed CY7C09379V information and also removed -6 speed bin information). Updated Switching Characteristics (Removed CY7C09379V information and also removed -6 speed bin information). Updated Ordering Information (Removed part CY7C09279V-7AC). Updated Package Diagrams. Added Acronyms and Units of Measure. Updated to new template.
*H	3402091	10/12/2011	ADMU	Updated Ordering Information (Removed pruned part CY7C09289V-9AI). Updated Package Diagrams.
*	3680923	08/01/2012	ADMU / SMCH	Updated Pin Configurations (Updated Figure 2). Updated Switching Characteristics (Changed name of parameter from t_{CKZ} to t_{CKHZ} , changed name of parameter from t_{CKZ} to t_{CKLZ} in the next corresponding row). Updated Switching Waveforms (Updated Figure 15). Updated Address Counter Control Operation. Updated Ordering Information (Removed pruned part CY7C09289V-9AC). Updated Package Diagrams (spec 51-85048 (Changed revision from *E to *G)).
*J	3859909	01/07/2013	SMCH	Updated Ordering Information (Updated part numbers).
*К	4580622	11/27/2014	SMCH	Updated Functional Description: Added "For a complete list of related documentation, click here." at the end. Updated Package Diagrams: spec 51-85048 – Changed revision from *G to *I.
*L	4918880	09/14/2015	VINI	Updated Ordering Information (Updated part numbers). Updated to new template. Completing Sunset Review.



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Document Title: CY7C09269V/79V/89V/CY7C09369V/89V, 3.3 V 16K / 32K / 64K × 16 / 18 Synchronous Dual-Port Static RAM Document Number: 38-06056					
Revision	ECN	Submission Date	Orig. of Change	Description of Change	
*М	5183282	03/21/2016	VINI	Updated Pin Configurations: Updated Figure 1 (Fixed typo error in pin number 50). Updated Package Diagrams: spec 51-85048 – Changed revision from *I to *J. Updated to new template. Completing Sunset Review.	



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